

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	EV-IRFR3410-T1
▶ Overseas	Part Number	IRFR3410
▶ Equivalent	Part Number	IRFR3410

"T1" means TO-252

EV is the abbreviation of name EVVO

N-Channel Enhancement Mode MOSFET

Description

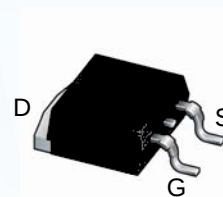
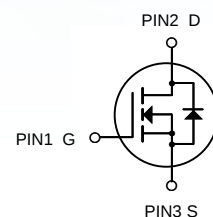
The EV-IRFR3410-T1 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features
 $V_{DS} = 100V$ $I_D = 30A$
 $R_{DS(ON)} < 48m\Omega$ @ $V_{GS}=10V$
Application

Battery protection

Load switch

Uninterruptible power supply

**TO-252**

N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
EV-IRFR3410-T1	TO-252	EVVOSEMI	2500

Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	30	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	13	A
I_{DM}	Pulsed Drain Current ²	80	A
EAS	Single Pulse Avalanche Energy ³	30	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	42	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	3.6	$^\circ C/W$

N-Channel Enhancement Mode MOSFET

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

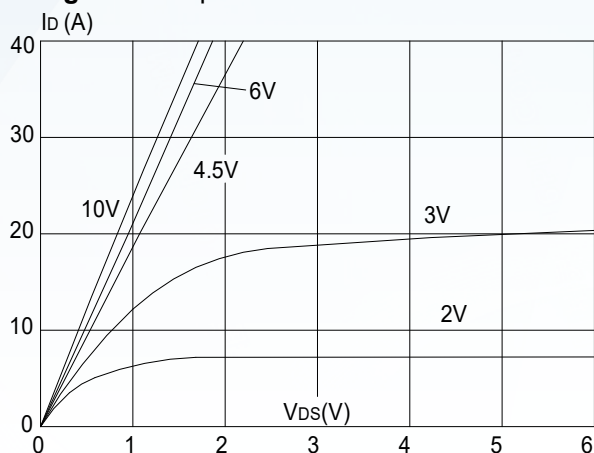
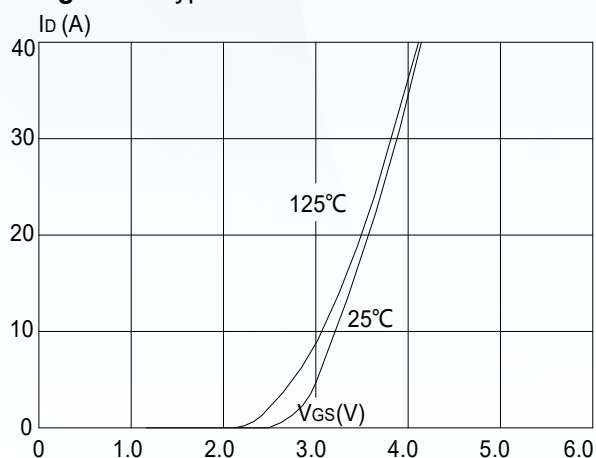
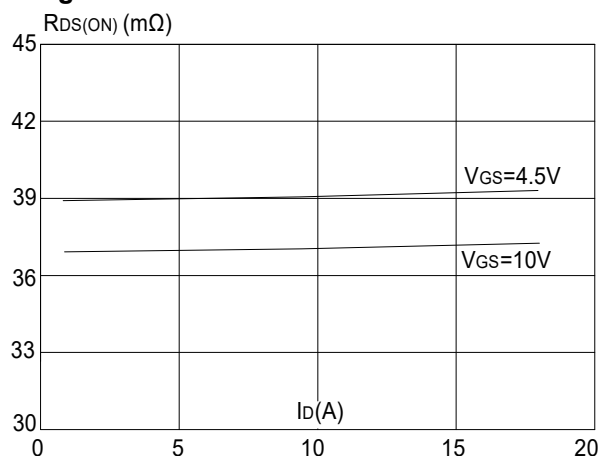
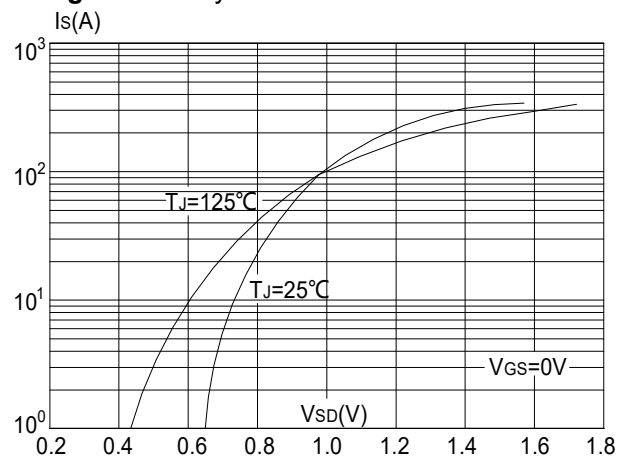
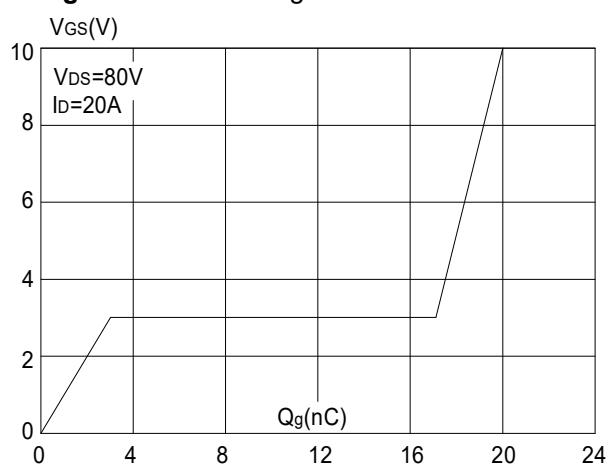
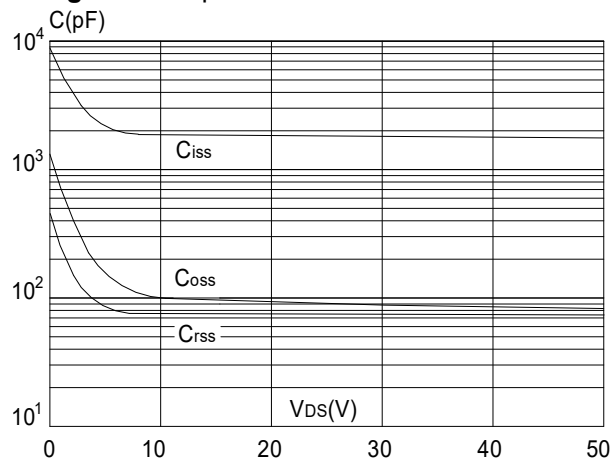
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.2	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =10A	-	37	48	mΩ
		V _{GS} =4.5V, I _D =6A	-	39	55	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	1964	-	pF
C _{oss}	Output Capacitance		-	90	-	pF
C _{rss}	Reverse Transfer Capacitance		-	74	-	pF
Q _g	Total Gate Charge	V _{DS} =80V, I _D =20A, V _{GS} =4.5V	-	20	-	nC
Q _{gs}	Gate-Source Charge		-	3.1	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	14	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =80V, I _D =20A, R _G =3.1Ω, V _{GS} =4.5V	-	11	-	ns
t _r	Turn-on Rise Time		-	91	-	ns
t _{d(off)}	Turn-off Delay Time		-	40	-	ns
t _f	Turn-off Fall Time		-	71	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	27	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =20A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=100A/μs	-	64	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	152	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

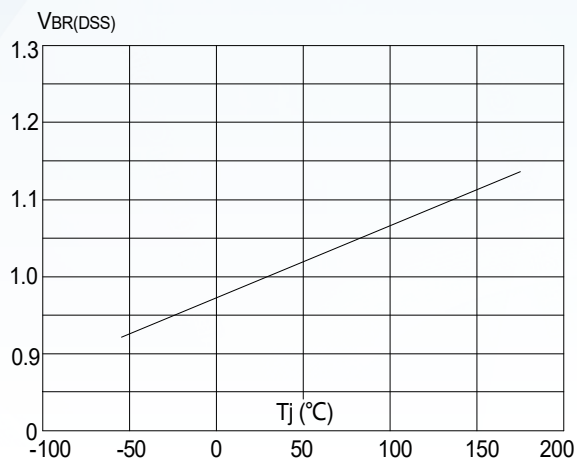
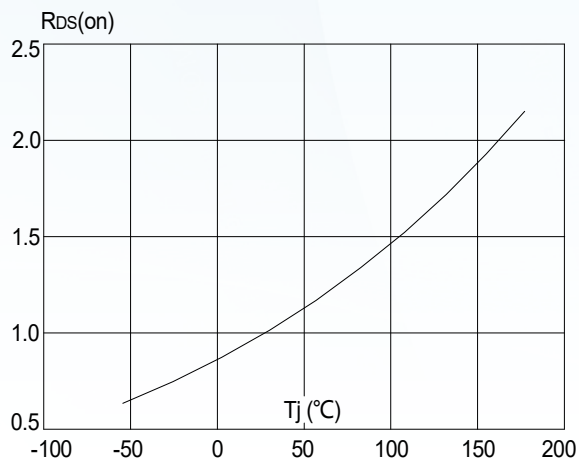
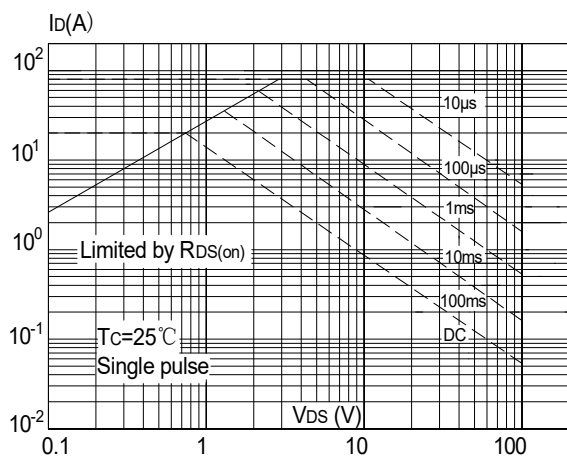
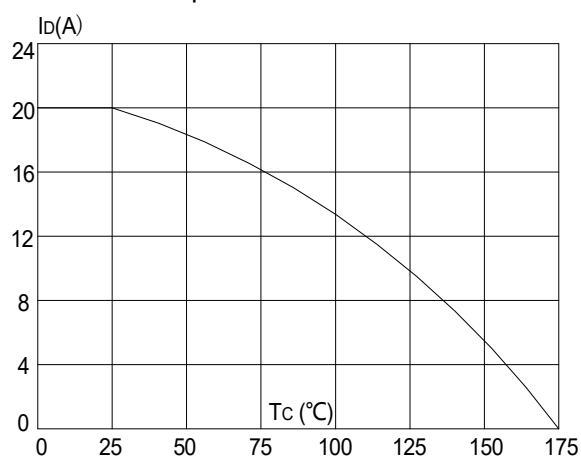
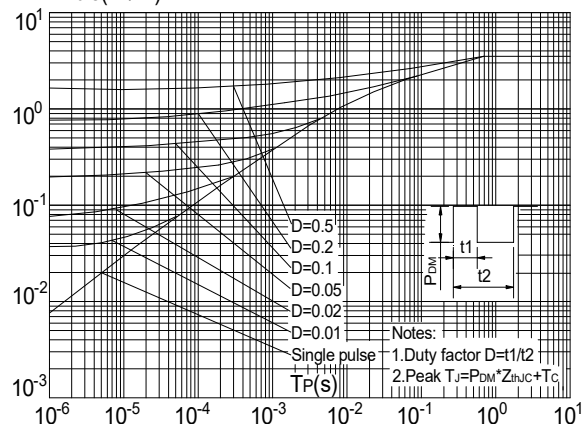
2. EAS condition : $T_J=25^\circ\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}= 11A$ 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

N-Channel Enhancement Mode MOSFET

Typical Performance Characteristics

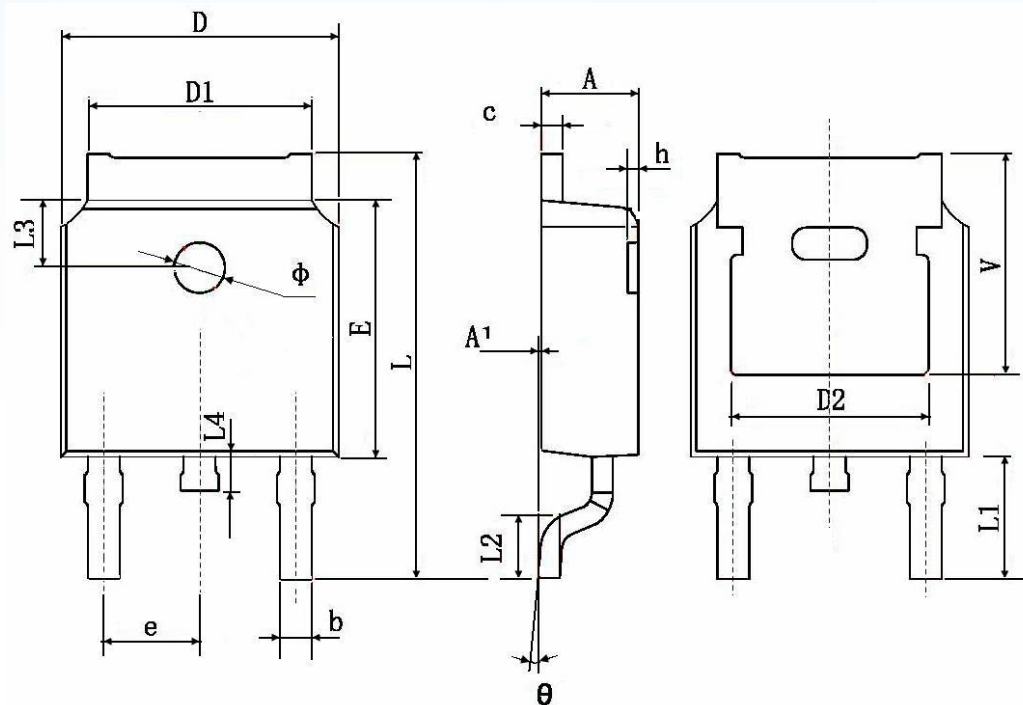
Figure 1: Output Characteristics**Figure 2: Typical Transfer Characteristics****Figure 3: On-resistance vs. Drain Current****Figure 4: Body Diode Characteristics****Figure 5: Gate Charge Characteristics****Figure 6: Capacitance Characteristics**

N-Channel Enhancement Mode MOSFET

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**Figure 8:** Normalized on Resistance vs. Junction Temperature**Figure 9:** Maximum Safe Operating Area**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case

N-Channel Enhancement Mode MOSFET

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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